

# Eugene Yakimov

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/1485641/publications.pdf>

Version: 2024-02-01

317  
papers

2,870  
citations

218592

26  
h-index

345118

36  
g-index

321  
all docs

321  
docs citations

321  
times ranked

1384  
citing authors

#	ARTICLE	IF	CITATIONS
1	Point defect induced degradation of electrical properties of Ga <sub>2</sub> O <sub>3</sub> by 10 <sup>16</sup> MeV proton damage. Applied Physics Letters, 2018, 112, .	1.5	98
2	What is the real value of diffusion length in GaN?. Journal of Alloys and Compounds, 2015, 627, 344-351.	2.8	63
3	Defects responsible for charge carrier removal and correlation with deep level introduction in irradiated <sup>67</sup> Zn-Ga <sub>2</sub> O <sub>3</sub> . Applied Physics Letters, 2018, 113, .	1.5	62
4	Diffusion length of non-equilibrium minority charge carriers in <sup>67</sup> Zn-Ga <sub>2</sub> O <sub>3</sub> measured by electron beam induced current. Journal of Applied Physics, 2018, 123, .	1.1	50
5	EBIC measurements of small diffusion length in semiconductor structures. Semiconductors, 2007, 41, 411-413.	0.2	49
6	On the real structure of monocrystalline silicon near dislocation slip planes. Physica Status Solidi A, 1981, 68, 53-60.	1.7	44
7	Spatial variations of doping and lifetime in epitaxial laterally overgrown GaN. Applied Physics Letters, 2007, 90, 152114.	1.5	43
8	Crystal structure, vibrational spectroscopy and optical properties of a one-dimensional organic-inorganic hybrid perovskite of [NH <sub>3</sub> CH <sub>2</sub> CH(NH <sub>3</sub> )CH <sub>2</sub> ]BiCl <sub>5</sub> . Acta Crystallographica Section B: Structural Science, Crystal Engineering and Materials, 2019, 75, 880-886.	0.5	43
9	The effect of thermal treatment on the electrical activity and mobility of dislocations in Si. Physica Status Solidi A, 1980, 60, 341-349.	1.7	41
10	Electrical Properties, Deep Trap and Luminescence Spectra in Semi-Insulating, Czochralski <sup>67</sup> Zn-Ga <sub>2</sub> O <sub>3</sub> (Mg). ECS Journal of Solid State Science and Technology, 2019, 8, Q3019-Q3023.	0.9	41
11	Effects of laterally overgrown n-GaN thickness on defect and deep level concentrations. Journal of Vacuum Science & Technology B, 2008, 26, 990.	1.3	39
12	Hydrogen plasma treatment of <sup>67</sup> Zn-Ga <sub>2</sub> O <sub>3</sub> : Changes in electrical properties and deep trap spectra. Applied Physics Letters, 2019, 115, .	1.5	39
13	Donor nonuniformity in undoped and Si doped n-GaN prepared by epitaxial lateral overgrowth. Applied Physics Letters, 2008, 92, 042118.	1.5	38
14	Nonradiative recombination dynamics in InGaN/GaN LED defect system. Superlattices and Microstructures, 2009, 45, 301-307.	1.4	38
15	Electron-beam-induced-current study of defects in GaN; experiments and simulation. Journal of Physics Condensed Matter, 2002, 14, 13069-13077.	0.7	37
16	Defects at the surface of <sup>67</sup> Zn-Ga <sub>2</sub> O <sub>3</sub> produced by Ar plasma exposure. APL Materials, 2019, 7, .	2.2	36
17	Deep trap spectra of Sn-doped <sup>67</sup> Zn-Ga <sub>2</sub> O <sub>3</sub> grown by halide vapor phase epitaxy on sapphire. APL Materials, 2019, 7, .	2.2	35
18	Deep level defect states in <sup>67</sup> Zn, <sup>67</sup> Zn, and <sup>67</sup> Zn-Ga <sub>2</sub> O <sub>3</sub> crystals and films: Impact on device performance. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, .	0.9	35

#	ARTICLE	IF	CITATIONS
19	Editorsâ€™ Choiceâ€™”Electrical Properties and Deep Traps in $\text{In}_2\text{Ga}_2\text{O}_3$ :Sn Films Grown on Sapphire by Halide Vapor Phase Epitaxy. ECS Journal of Solid State Science and Technology, 2020, 9, 045003.	0.9	34
20	Neutron Radiation Effects in Epitaxially Laterally Overgrown GaN Films. Journal of Electronic Materials, 2007, 36, 1320-1325.	1.0	30
21	Betavoltaic battery performance: Comparison of modeling and experiment. Applied Radiation and Isotopes, 2018, 137, 184-189.	0.7	30
22	Photosensitivity of $\text{Ga}_2\text{O}_3$ Schottky diodes: Effects of deep acceptor traps present before and after neutron irradiation. APL Materials, 2020, 8, .	2.2	30
23	Annealing effect on the electrical activity of extended defects in plastically deformed p-Si with low dislocation density. Physica Status Solidi (A) Applications and Materials Science, 2005, 202, 896-900.	0.8	29
24	Recombination properties of dislocation slip planes. Physica Status Solidi A, 1986, 95, 173-177.	1.7	28
25	Deep traps determining the non-radiative lifetime and defect band yellow luminescence in n-GaN. Journal of Alloys and Compounds, 2016, 686, 1044-1052.	2.8	28
26	Temperature dependence of dislocation efficiency as sinks for self-interstitials in silicon as measured by gold diffusion. Journal of Applied Physics, 1995, 78, 1495-1499.	1.1	27
27	On the nature of hydrogen-related centers in p-type irradiated silicon. Physica B: Condensed Matter, 2001, 308-310, 210-212.	1.3	27
28	Electrical, luminescent, and deep trap properties of Si doped n-GaN grown by pendeo epitaxy. Journal of Applied Physics, 2016, 119, .	1.1	27
29	Defects responsible for lifetime degradation in electron irradiated n-GaN grown by hydride vapor phase epitaxy. Applied Physics Letters, 2017, 110, .	1.5	26
30	Recombination properties of dislocations in GaN. Journal of Applied Physics, 2018, 123, 161543.	1.1	26
31	Experimental estimation of electronâ€“hole pair creation energy in $\text{In}_2\text{Ga}_2\text{O}_3$ . Applied Physics Letters, 2021, 118, .	1.5	26
32	Studies of deep level centers determining the diffusion length in epitaxial layers and crystals of undoped n-GaN. Journal of Applied Physics, 2016, 119, .	1.1	25
33	Movement of basal plane dislocations in GaN during electron beam irradiation. Applied Physics Letters, 2015, 106, .	1.5	24
34	Point defects controlling non-radiative recombination in GaN blue light emitting diodes: Insights from radiation damage experiments. Journal of Applied Physics, 2017, 122, .	1.1	24
35	Electrical Properties, Deep Levels and Luminescence Related to Fe in Bulk Semi-Insulating $\text{In}_2\text{Ga}_2\text{O}_3$ Doped with Fe. ECS Journal of Solid State Science and Technology, 2019, 8, Q3091-Q3096.	0.9	24
36	Contribution of the disturbed dislocation slip planes to the electrical properties of plastically deformed silicon. Physica B: Condensed Matter, 2003, 340-342, 1005-1008.	1.3	23

#	ARTICLE	IF	CITATIONS
37	Hydrogen penetration into silicon during wet-chemical etching. <i>Microelectronic Engineering</i> , 2003, 66, 320-326.	1.1	23
38	On the nature of photosensitivity gain in Ga <sub>2</sub> O <sub>3</sub> Schottky diode detectors: Effects of hole trapping by deep acceptors. <i>Journal of Alloys and Compounds</i> , 2021, 879, 160394.	2.8	23
39	Anomalous electrical properties of dislocation slip plane in Si. <i>EPJ Applied Physics</i> , 2004, 27, 349-351.	0.3	22
40	Pulsed fast reactor neutron irradiation effects in Si doped n-type $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> . <i>Journal Physics D: Applied Physics</i> , 2020, 53, 274001.	1.3	22
41	EBIC Investigation of the Electrical Activity of Dislocations with Different Impurity Atmospheres in Si. <i>Physica Status Solidi A</i> , 1990, 122, 121-128.	1.7	20
42	High-resolution electron-beam-induced-current study of the defect structure in GaN epilayers. <i>Journal of Physics Condensed Matter</i> , 2002, 14, 13285-13290.	0.7	19
43	Dissociation of iron-related centers in Si stimulated by hydrogen. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000, 71, 268-271.	1.7	18
44	Two channels of non-radiative recombination in InGaN/GaN LEDs. <i>Physica B: Condensed Matter</i> , 2009, 404, 4896-4898.	1.3	18
45	Effect of low-energy electron irradiation on the cathodoluminescence of multiple quantum well (MQW) InGaN/GaN structures. <i>Solid State Communications</i> , 2011, 151, 208-211.	0.9	18
46	Trapping of gold by nanocavities induced by H <sup>+</sup> or He <sup>++</sup> implantation in float zone and Czochralski grown silicon wafers. <i>Journal of Applied Physics</i> , 2001, 90, 2806-2812.	1.1	17
47	Recombination and optical properties of dislocations gliding at room temperature in GaN under applied stress. <i>Journal of Alloys and Compounds</i> , 2019, 776, 181-186.	2.8	17
48	Minority carrier lifetime scan maps applied to iron concentration mapping in silicon wafers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002, 91-92, 216-219.	1.7	16
49	Diffusion length measurements in GaN. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 05FH04.	0.8	16
50	Role of hole trapping by deep acceptors in electron-beam-induced current measurements in $\hat{\Gamma}^2$ -Ga <sub>2</sub> O <sub>3</sub> vertical rectifiers. <i>Journal Physics D: Applied Physics</i> , 2020, 53, 495108.	1.3	16
51	Simulation of hydrogen penetration into p-type silicon under wet chemical etching. <i>Semiconductors</i> , 2002, 36, 282-285.	0.2	15
52	Temperature dependence of electron beam induced current contrast of deformation-induced defects in silicon. <i>Journal of Physics Condensed Matter</i> , 2004, 16, S201-S205.	0.7	15
53	Electrical and luminescent properties and deep traps spectra in GaN nanopillar layers prepared by dry etching. <i>Journal of Applied Physics</i> , 2012, 112, 073112.	1.1	15
54	Comparison between the EBIC and XBIC contrasts of dislocations and grain boundaries. <i>Journal of Surface Investigation</i> , 2012, 6, 894-896.	0.1	15

#	ARTICLE	IF	CITATIONS
55	Study of the properties of silicon-based semiconductor converters for betavoltaic cells. Semiconductors, 2015, 49, 746-748.	0.2	15
56	Deep Electron Traps Responsible for Higher Quantum Efficiency in Improved GaN/InGaN Light Emitting Diodes Embedded with SiO <sub>2</sub> Nanoparticles. ECS Journal of Solid State Science and Technology, 2016, 5, Q274-Q277.	0.9	15
57	Hydrogen interaction with defects in electron-irradiated silicon. Physica B: Condensed Matter, 1999, 273-274, 235-238.	1.3	14
58	Peculiarities of extended defect system in III-nitrides with different degrees of order of mosaic structure. Physica B: Condensed Matter, 2003, 340-342, 462-465.	1.3	14
59	EBIC and CL studies of ELOG GaN films. Superlattices and Microstructures, 2009, 45, 308-313.	1.4	14
60	Metastable centers in AlGaN/AlN/GaN heterostructures. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, .	0.6	14
61	Cathodoluminescence and electron beam induced current investigations of stacking faults mechanically introduced in 4H-SiC in the brittle domain. Journal of Applied Physics, 2013, 114, .	1.1	14
62	Comparison of the efficiency of <sup>63</sup> Ni beta-radiation detectors made from silicon and wide-gap semiconductors. Journal of Surface Investigation, 2014, 8, 843-845.	0.1	14
63	Electron traps as major recombination centers in n-GaN films grown by metalorganic chemical vapor deposition. Applied Physics Express, 2016, 9, 061002.	1.1	14
64	Electrical properties and deep trap spectra in Ga <sub>2</sub> O <sub>3</sub> films grown by halide vapor phase epitaxy on p-type diamond substrates. Journal of Applied Physics, 2021, 129, .	1.1	14
65	Plasma Stimulated Impurity Redistribution in Silicon. Physica Status Solidi A, 1989, 111, 81-88.	1.7	13
66	SEM/EBIC investigations of extended defect system in GaN epilayers. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1797-1801.	0.8	13
67	SEM-EBIC investigation of silicon, compensated by zinc during high temperature diffusion annealing. Journal of Materials Science: Materials in Electronics, 2008, 19, 277-280.	1.1	13
68	Simulation of the current induced by <sup>63</sup> Ni beta radiation. Journal of Surface Investigation, 2013, 7, 852-855.	0.1	13
69	Electrical properties of undoped GaN films grown by maskless epitaxial lateral overgrowth. Journal of Applied Physics, 2013, 113, .	1.1	13
70	Heterostructure optimization for increasing LED efficiency. Japanese Journal of Applied Physics, 2016, 55, 05FJ13.	0.8	13
71	Prediction of betavoltaic battery output parameters based on SEM measurements and Monte Carlo simulation. Applied Radiation and Isotopes, 2016, 112, 98-102.	0.7	13
72	Structural and electrical properties of thick <sup>63</sup> Ni-Ga <sub>2</sub> O <sub>3</sub> grown on GaN/sapphire templates. APL Materials, 2022, 10, .	2.2	13

#	ARTICLE	IF	CITATIONS
73	Asymmetry of isolated dislocation mobility in Silicon single crystals. <i>Crystal Research and Technology</i> , 1984, 19, 295-302.	0.6	12
74	Influence of the deformation on the luminescence properties of Si light-emitting diodes. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005, 2, 1842-1846.	0.8	12
75	EBIC characterization of light-emitting structures based on GaN. <i>Semiconductors</i> , 2007, 41, 491-494.	0.2	12
76	Electrical, optical, and structural properties of GaN films prepared by hydride vapor phase epitaxy. <i>Journal of Alloys and Compounds</i> , 2014, 617, 200-206.	2.8	12
77	Electrical, Luminescent and Structural Properties of Nanopillar GaN/InGaN Multi-Quantum-Well Structures Prepared by Dry Etching. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, Q165-Q170.	0.9	12
78	Effect of low energy electron beam irradiation on Shockley partial dislocations bounding stacking faults introduced by plastic deformation in 4H-SiC in its brittle temperature range. <i>Superlattices and Microstructures</i> , 2016, 99, 226-230.	1.4	12
79	Structure and recombination properties of extended defects in the dislocation slip plane in silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 3100-3104.	0.8	11
80	Comment on "Carrier recombination near threading dislocations in GaN epilayers by low voltage cathodoluminescence" [Appl. Phys. Lett. 89, 161905 (2006)]. <i>Applied Physics Letters</i> , 2010, 97, 166101.	1.5	11
81	Effect of metal contamination on recombination properties of extended defects in multicrystalline Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 1942-1946.	0.8	11
82	Radiation enhanced basal plane dislocation glide in GaN. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 05FM03.	0.8	11
83	Development of betavoltaic cell technology production based on microchannel silicon and its electrical parameters evaluation. <i>Applied Radiation and Isotopes</i> , 2017, 121, 71-75.	0.7	11
84	Quantum Barrier Growth Temperature Affects Deep Traps Spectra of InGaN Blue Light Emitting Diodes. <i>ECS Journal of Solid State Science and Technology</i> , 2018, 7, Q80-Q84.	0.9	11
85	Electrical properties of $\text{In}_x\text{Ga}_{1-x}\text{O}_3$ films grown by halide vapor phase epitaxy on sapphire with $\text{In}_x\text{Cr}_{2-x}\text{O}_3$ buffers. <i>Journal of Applied Physics</i> , 2022, 131, .	1.1	11
86	Point defect creation by proton and carbon irradiation of $\text{In}_x\text{Ga}_{1-x}\text{O}_3$ . <i>Journal of Applied Physics</i> , 2022, 132, .	1.1	11
87	"Apparatus" electron beam microtomography in SEM. <i>Physica Status Solidi A</i> , 1995, 150, 211-219.	1.7	10
88	Dislocation-Point Defect Interaction Effect on Local Electrical Properties of Semiconductors. <i>Journal De Physique III</i> , 1997, 7, 2293-2307.	0.3	10
89	Oxygen Effect on Electrical and Optical Properties of Dislocations in Silicon. <i>Physica Status Solidi A</i> , 1999, 171, 341-346.	1.7	10
90	Nitrogen effect on self-interstitial generation in Czochralski silicon revealed by gold diffusion experiments. <i>Journal of Applied Physics</i> , 2001, 90, 3642-3644.	1.1	10

#	ARTICLE	IF	CITATIONS
91	Electrical properties of dislocation trails in n-Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 3105-3109.	0.8	10
92	Effect of low energy electron irradiation on optical properties of InGaN/GaN light emitting structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 1265-1268.	0.8	10
93	Properties of nanopillar structures prepared by dry etching of undoped GaN grown by maskless epitaxial overgrowth. <i>Journal of Alloys and Compounds</i> , 2013, 554, 258-263.	2.8	10
94	Capacitance-voltage and admittance investigations of InGaN/GaN MQW LEDs: frequency dependence. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 338-341.	0.8	10
95	Low temperature stacking fault nucleation and expansion from stress concentrators in 4H-SiC. <i>Acta Materialia</i> , 2017, 139, 155-162.	3.8	10
96	Study of Wide-Gap Semiconductors Using Electron-Beam Induced Current Method. <i>Crystallography Reports</i> , 2021, 66, 581-593.	0.1	10
97	Electrical Properties and Defect Structure of Plastically Deformed Silicon Crystals Doped with Gold. <i>Physica Status Solidi A</i> , 1987, 102, 687-695.	1.7	9
98	EBIC investigation of InGaN/GaN multiple quantum well structures irradiated with low energy electrons. <i>Journal of Physics: Conference Series</i> , 2011, 281, 012013.	0.3	9
99	Study of the effect of irradiation with the SEM electron beam on cathodoluminescence and the induced current in InGaN/GaN structures with multiple quantum wells. <i>Journal of Surface Investigation</i> , 2011, 5, 945-948.	0.1	9
100	Calculating the extended defect contrast for the X-ray-beam-induced current method. <i>Technical Physics Letters</i> , 2012, 38, 913-916.	0.2	9
101	The Electrical Activity of Dislocation Slip Planes in Semiconductor Crystals. <i>Materials Science Forum</i> , 1986, 10-12, 787-790.	0.3	8
102	Scanning electron microscopy in submicron structure diagnostics. <i>Vacuum</i> , 1988, 38, 1045-1050.	1.6	8
103	Spatial distribution of dislocation-related centers in plastically deformed silicon. <i>Physica Status Solidi A</i> , 1991, 127, 67-73.	1.7	8
104	Phosphorus diffusion effect on defect structure of silicon with oxygen precipitates revealed by gold diffusion study. <i>Applied Physics Letters</i> , 1995, 67, 2054-2056.	1.5	8
105	Application of Surface Electron Beam Induced Voltage Method for the Contactless Characterization of Semiconductor Structures. <i>Solid State Phenomena</i> , 1998, 63-64, 327-332.	0.3	8
106	Impact of thermal annealing on deep-level defects in strained-Si <sup>δ</sup> -SiGe heterostructure. <i>Journal of Applied Physics</i> , 2008, 103, 103506.	1.1	8
107	Neutron doping effects in epitaxially laterally overgrown n-GaN. <i>Applied Physics Letters</i> , 2011, 98, .	1.5	8
108	Microcathodoluminescence spectra evolution for planar and nanopillar multi-quantum-well GaN-based structures as a function of electron irradiation dose. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014, 32, 011207.	0.6	8

#	ARTICLE	IF	CITATIONS
109	Some new insights into the impact of annealing on single stacking faults in 4H-SiC. Superlattices and Microstructures, 2018, 120, 7-14.	1.4	8
110	SEM investigation of semiconductors by the capacitance techniques. Microelectronic Engineering, 1990, 12, 179-185.	1.1	7
111	The Peculiarities of Deep Level Defect Passivation in Si by Atomic Hydrogen. Physica Status Solidi A, 1990, 120, 391-395.	1.7	7
112	Effect of irradiation in sem on electrical properties of silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 42, 274-276.	1.7	7
113	Interaction of gold with dislocations in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 71, 272-275.	1.7	7
114	Effect of mesoscopic inhomogeneities on the critical current of bulk melt-textured YBCO. Physica C: Superconductivity and Its Applications, 2003, 390, 127-133.	0.6	7
115	Electrical and Optical Properties of Dislocations Generated under Pure Conditions. Solid State Phenomena, 2003, 95-96, 453-458.	0.3	7
116	EBIC investigations of GaN layers prepared by epitaxial lateral overgrowth. Journal of Surface Investigation, 2008, 2, 688-691.	0.1	7
117	Electrical properties and deep traps spectra in undoped M-plane GaN films prepared by standard MOCVD and by selective lateral overgrowth. Journal of Crystal Growth, 2009, 311, 2923-2925.	0.7	7
118	Study of dislocation EBIC image width in GaN films and GaN based structures. Journal of Surface Investigation, 2009, 3, 58-60.	0.1	7
119	Frequency and temperature dependences of capacitance-voltage characteristics of InGaN/GaN light-emitting structures with multiple quantum wells. Semiconductors, 2011, 45, 221-224.	0.2	7
120	Electrical properties of plastically deformed silicon due to its interaction with an iron impurity. Physics of the Solid State, 2011, 53, 1240-1243.	0.2	7
121	X-ray beam induced current method at the laboratory x-ray source. Review of Scientific Instruments, 2011, 82, 093702.	0.6	7
122	XBIC Investigation of the Grain Boundaries in Multicrystalline Si on the Laboratory X-Ray Source. Solid State Phenomena, 0, 178-179, 226-229.	0.3	7
123	Application of a scanning electron microscope in simulating a beta-emission-induced current. Journal of Surface Investigation, 2013, 7, 81-84.	0.1	7
124	Analysis of the temperature dependence of the capacitance-voltage characteristics of InGaN/GaN multiple quantum well light-emitting structures. Semiconductors, 2013, 47, 162-168.	0.2	7
125	Photoluminescence enhancement by localized surface plasmons in AlGaIn/GaN/AlGaIn double heterostructures. Physica Status Solidi - Rapid Research Letters, 2015, 9, 575-579.	1.2	7
126	Effects of Hydrogen Plasma Treatment Condition on Electrical Properties of $\text{In}_{2-x}\text{Ga}_x\text{O}_3$ . ECS Journal of Solid State Science and Technology, 2019, 8, P661-P666.	0.9	7



#	ARTICLE	IF	CITATIONS
127	Electron beam induced excess carrier concentration. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2017, 14, 1600266.	0.8	7
128	1â€‰GeV proton damage in Î²-Ga <sub>2</sub> O <sub>3</sub> . <i>Journal of Applied Physics</i> , 2021, 130, .	1.1	7
129	Degradation by sidewall recombination centers in GaN blue micro-LEDs at diameters&lt;30Âµm. <i>Journal of Alloys and Compounds</i> , 2022, 921, 166072.	2.8	7
130	The Influence of Thermal Treatment on Thermally Stimulated Depolarization Spectrum of the Electret State in Plastically Deformed Silicon. <i>Physica Status Solidi A</i> , 1984, 84, 443-450.	1.7	6
131	Possibilities of modulated cathodoluminescence for multilayer structure characterization. <i>Scanning</i> , 1993, 15, 31-36.	0.7	6
132	Gold and platinum profiles in fast power devices. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2000, 71, 166-170.	1.7	6
133	Correlation of diffusion length and trap concentration with dislocation density in MOCVD-grown GaN. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 479-483.	1.3	6
134	Gold Diffusion as a Tool for Defect Characterization in Si. <i>Solid State Phenomena</i> , 2003, 95-96, 495-500.	0.3	6
135	Characterization of silicon ribbon by the SEM methods. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 1384-1387.	0.8	6
136	Cathodoluminescence study of individual ZnO nanorods. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 1403-1406.	0.8	6
137	Investigation of electrical and optical properties in semiconductor structures via SEM techniques with high spatial resolution. <i>Journal of Surface Investigation</i> , 2012, 6, 887-889.	0.1	6
138	Influence of metal impurities on recombination activity of dislocations in multicrystalline silicon. <i>Semiconductors</i> , 2013, 47, 232-234.	0.2	6
139	Low energy electron irradiation effect on optical and electrical properties of InGaN/GaN multiple quantum well structures. <i>International Journal of Nanoparticles</i> , 2013, 6, 191.	0.1	6
140	Structural defects responsible for excessive leakage current in Schottky diodes prepared on undoped n-GaN films grown by hydride vapor phase epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014, 32, 051212.	0.6	6
141	Characterization of Si Convertors of Beta-Radiation in the Scanning Electron Microscope. <i>Solid State Phenomena</i> , 2015, 242, 312-315.	0.3	6
142	EBIC and LBIC investigations of dislocation trails in Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015, 12, 1081-1084.	0.8	6
143	EBIC investigations of dislocations in ELOG GaN. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015, 12, 1132-1135.	0.8	6
144	Increase in the diffusion length of minority carriers in Al <sub>x</sub> Ga <sub>1-x</sub> N alloys (x = 0â€‰0.1) fabricated by ammonia molecular beam epitaxy. <i>Semiconductors</i> , 2015, 49, 1285-1289.	0.2	6

#	ARTICLE	IF	CITATIONS
145	Recombination activity of interfaces in multicrystalline silicon. <i>Semiconductors</i> , 2015, 49, 724-728.	0.2	6
146	EFFECT OF DISLOCATIONS ON THE LOCAL ELECTRICAL PROPERTIES OF N-SI. , 1990, , 1443-1446.		6
147	GaAs diodes for TiT2-based betavoltaic cells. <i>Applied Radiation and Isotopes</i> , 2022, 179, 110030.	0.7	6
148	Simulation of recombination contrast of extended defects in the modulated EBIC. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1996, 42, 176-180.	1.7	5
149	Oxygen precipitate precursors and low temperature gettering processes. II. DLTS analysis of deep levels associated to oxide precipitates. <i>Materials Science in Semiconductor Processing</i> , 1999, 2, 69-74.	1.9	5
150	Electroluminescent Properties of Strained p-Si LEDs. <i>Semiconductors</i> , 2005, 39, 1229.	0.2	5
151	Comparative study of quantum efficiency of blue LED with different nanostructural arrangement. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 2981-2985.	0.8	5
152	Defects with bright contrast in the induced-current mode in GaN-based light-emitting structures. <i>Journal of Surface Investigation</i> , 2007, 1, 394-397.	0.1	5
153	EBIC characterization of strained Si/SiGe heterostructures. <i>Semiconductors</i> , 2007, 41, 402-406.	0.2	5
154	EBIC Characterization of Light Emitting Structures Containing InGaN/GaN MQW. <i>Springer Proceedings in Physics</i> , 2008, , 481-484.	0.1	5
155	EBIC investigations of defect distribution in ELOG GaN films. <i>Physica B: Condensed Matter</i> , 2009, 404, 4916-4918.	1.3	5
156	Effect of the silicon doping level and features of nanostructural arrangement on decrease in external quantum efficiency in InGaN/GaN light-emitting diodes with increasing current. <i>Semiconductors</i> , 2011, 45, 415-421.	0.2	5
157	Influence of electron-beam irradiation in SEM on the cathodoluminescence and electron-beam-induced current in InGaN/GaN light-emitting diodes with a buried active region. <i>Journal of Surface Investigation</i> , 2012, 6, 890-893.	0.1	5
158	Role of extended defects in the transformation of InGaN/GaN multiple quantum well structure optical properties under low energy electron beam irradiation. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013, 10, 464-467.	0.8	5
159	Spatial Distribution of the Dislocation Trails in Silicon. <i>Solid State Phenomena</i> , 2015, 242, 155-159.	0.3	5
160	Effect of low-energy electron irradiation on the optical properties of structures containing multiple InGaN/GaN quantum well. <i>Semiconductors</i> , 2015, 49, 143-148.	0.2	5
161	Estimations of Low Temperature Dislocation Mobility in GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900163.	0.8	5
162	Radiation-enhanced dislocation glide in 4H-SiC at low temperatures. <i>Journal of Alloys and Compounds</i> , 2020, 837, 155470.	2.8	5

#	ARTICLE	IF	CITATIONS
163	Grown and Characterization of ZnO Aligned Nanorod Arrays for Sensor Applications. <i>Energies</i> , 2021, 14, 3750.	1.6	5
164	Dislocations introduced in n-GaN at room temperature cause conductivity inversion. <i>Journal of Alloys and Compounds</i> , 2021, 877, 160281.	2.8	5
165	Dislocation trails in Si: Geometry and electrical properties. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2017, 14, 1700074.	0.8	5
166	Potential relief in PbTe:In(Cd) heterophase systems. <i>Journal of Physics and Chemistry of Solids</i> , 1990, 51, 1333-1338.	1.9	4
167	Mapping of diffusion length and depletion region width in Schottky diodes. <i>Semiconductor Science and Technology</i> , 1992, 7, A171-A174.	1.0	4
168	Low temperature hydrogenation of dislocated Si. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999, 58, 60-63.	1.7	4
169	Simulation of hydrogen penetration in silicon under wet chemical etching. <i>Physica B: Condensed Matter</i> , 2001, 308-310, 213-215.	1.3	4
170	Nitrogen effect on gold diffusion in Cz Si. <i>Physica B: Condensed Matter</i> , 2001, 308-310, 396-399.	1.3	4
171	Study of depth distribution of metastable hydrogen-related defects in n-type GaAs. <i>Physica B: Condensed Matter</i> , 2001, 308-310, 827-830.	1.3	4
172	Annealing behavior of the system of metastable hydrogen-related defects M3/M4 in n-GaAs. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 341-344.	1.3	4
173	Investigation of characteristics of InSb-based photodiode linear arrays. <i>Semiconductors</i> , 2004, 38, 480-485.	0.2	4
174	Effect of dislocation trails on gold diffusion in Si. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009, 6, 1823-1826.	0.8	4
175	Investigations of electron beam induced conductivity in silicon oxide thin films. <i>Journal of Surface Investigation</i> , 2010, 4, 754-757.	0.1	4
176	A Comparison of EBIC, LBIC and XBIC Methods as Tools for Multicrystalline Si Characterization. <i>Solid State Phenomena</i> , 0, 205-206, 142-147.	0.3	4
177	DEEP TRAPS SPECTRA IN UNDOPEd GAN FILMS GROWN BY HYDRIDE VAPOR PHASE EPITAXY UNDER VARIOUS CONDITIONS. <i>American Journal of Applied Sciences</i> , 2014, 11, 1714-1721.	0.1	4
178	Defect detection in solar cells via electroluminescence, LBIC, and EBIC methods. <i>Journal of Surface Investigation</i> , 2014, 8, 839-842.	0.1	4
179	Investigation of nitride films by the electron-beam-induced current method. <i>Journal of Surface Investigation</i> , 2015, 9, 939-943.	0.1	4
180	Development and investigation of silicon converter beta radiation <sup>63</sup> Ni isotope. <i>IOP Conference Series: Materials Science and Engineering</i> , 2016, 110, 012029.	0.3	4

#	ARTICLE	IF	CITATIONS
181	Extended defect study in Si: EBIC versus LBIC. Superlattices and Microstructures, 2016, 99, 202-207.	1.4	4
182	Annealing and LEEBI Effects on the Stacking Fault Expansion and Shrinking in 4H-SiC. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900151.	0.8	4
183	Thermoresistive Semiconductor SiC/Si Composite Material. Semiconductors, 2019, 53, 220-223.	0.2	4
184	Study of single-layer stacking faults in 4H-SiC by deep level transient spectroscopy. Applied Physics Letters, 2020, 116, .	1.5	4
185	Charging Effects in Al-SiO <sub>2</sub> -p-Si Structures After Low-Energy Electron Beam Irradiation. Journal of Electronic Materials, 2020, 49, 5178-5183.	1.0	4
186	Betavoltaic cell based on Ni <sup>63</sup> -Ga <sub>2</sub> O <sub>3</sub> and <sup>63</sup> Ni source. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2022, 40, .	0.9	4
187	EBIC-Investigation of the Dislocation-Impurity Interaction in Silicon. Solid State Phenomena, 1991, 1-2, 59-63.	0.3	3
188	Modulated electron-beam-induced current and cathodoluminescence. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1994, 24, 23-27.	1.7	3
189	Modulated cathodoluminescence for extended defect characterization. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1994, 24, 121-123.	1.7	3
190	Hydrogen Stimulated Destruction of Fe-B Pairs in p-Si. Solid State Phenomena, 1997, 57-58, 383-386.	0.3	3
191	Interaction of hydrogen with radiation defects in p-Si crystals. Semiconductors, 2001, 35, 1355-1360.	0.2	3
192	Multi-electrode LBIC method for characterization of 1D "hidden" defects. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 91-92, 260-263.	1.7	3
193	EBIC Characterization of III-Nitride Structures Using Multifractal Parameterization. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 457-460.	0.8	3
194	EBIC characterization of HgCdTe based photoconductive elements. , 2005, 5834, 242.		3
195	Simulation and measurements of EBIC images of photoconductive elements based on HgCdTe. Semiconductors, 2007, 41, 407-410.	0.2	3
196	Profile of EBIC dislocation contrast in semiconductors with small diffusion length. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 1983-1986.	0.8	3
197	Comparison of extended-defect contrasts calculated in the XBIC and EBIC methods. Journal of Surface Investigation, 2010, 4, 709-711.	0.1	3
198	Recombination Activity of Twin Boundaries in Silicon Ribbons. Solid State Phenomena, 2011, 178-179, 106-109.	0.3	3

#	ARTICLE	IF	CITATIONS
199	Electrical and optical properties of stacking faults introduced by plastic deformation in 4H-SiC. , 2014, , .		3
200	Effect of copper on the recombination activity of extended defects in silicon. Semiconductors, 2015, 49, 716-719.	0.2	3
201	EBIC and LBIC studies of the properties of extended defects in plastically deformed silicon. Semiconductors, 2015, 49, 720-723.	0.2	3
202	MBE-grown AlGaIn/GaN heterostructures for UV photodetectors. Technical Physics, 2015, 60, 546-552.	0.2	3
203	Indium doping-induced change in the photoconduction spectra of o-TaS <sub>3</sub> . Physica B: Condensed Matter, 2015, 460, 180-184.	1.3	3
204	Recombination Processes in 4H-SiC pn Structures. Materials Science Forum, 2016, 858, 345-348.	0.3	3
205	Electrical Activity of Extended Defects in Multicrystalline Silicon. Semiconductors, 2018, 52, 254-259.	0.2	3
206	Temperature Dependence of Low-Energy Electron Beam Irradiation Effect on Optical Properties of MQW InGaIn/GaN Structures. Physica Status Solidi (B): Basic Research, 2018, 255, 1700646.	0.7	3
207	Room-Temperature Ni Interaction with Deformation-Induced Defects in Si: A DLTS Study. Physica Status Solidi (A) Applications and Materials Science, 2019, 216, 1900326.	0.8	3
208	Simulation of the Parameters of a Titanium-Tritide-Based Beta-Voltaic Cell. Semiconductors, 2019, 53, 96-98.	0.2	3
209	Electron-Beam Domain Patterning in Sr <sub>0.61</sub> Ba <sub>0.39</sub> Nb <sub>2</sub> O <sub>6</sub> Crystals. Coatings, 2020, 10, 299.	1.2	3
210	Cathodoluminescence and EBIC investigations of stacking fault expansion in 4H-SiC due to e-beam irradiation at fixed points. Journal Physics D: Applied Physics, 2022, 55, 245101.	1.3	3
211	The EBIC contrast of dislocation slip planes in silicon. Physica Status Solidi A, 1984, 84, K43-K45.	1.7	2
212	Microtomography of semiconductor crystals in the EBIC mode. Journal of Crystal Growth, 1990, 103, 197-199.	0.7	2
213	Increase of Electrical Activity of Dislocations in Si during Plastic Deformation. Materials Science Forum, 1995, 196-201, 1183-1188.	0.3	2
214	Reconstruction of recombination properties of extended defects in Si. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 42, 270-273.	1.7	2
215	An investigation of the rate of Si self-interstitial annihilation at dislocations. Journal of Physics Condensed Matter, 1996, 8, 5685-5690.	0.7	2
216	Simulation of EBIC Contrast for Extended Defects Inclined to the Surface. Solid State Phenomena, 2001, 78-79, 73-78.	0.3	2

#	ARTICLE	IF	CITATIONS
217	Reconstruction of Diffusion Length Distribution by the Modulated EBIC and OBIC. Solid State Phenomena, 2001, 78-79, 79-88.	0.3	2
218	Investigations of Defects Introduced in 4H-SiC n-Type Epitaxial Layers by Hydrogen DC Plasma. Materials Science Forum, 2004, 457-460, 509-512.	0.3	2
219	Simulation of uncharged dislocation EBIC contrast at high excitation level. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 1822-1826.	0.8	2
220	Study of the electrical and optical properties of silicon containing oxygen precipitates. Journal of Surface Investigation, 2007, 1, 398-401.	0.1	2
221	Simulation of XBIC Contrast of Precipitates in Si. Solid State Phenomena, 0, 156-158, 247-250.	0.3	2
222	SEM Characterization of Silicon Layers Grown on Carbon Foil. Solid State Phenomena, 2009, 156-158, 473-476.	0.3	2
223	One more deep level related to the metastable hydrogen-related defects in n-GaAs epilayers. Physica B: Condensed Matter, 2009, 404, 5096-5098.	1.3	2
224	An application of gold diffusion for defect investigation in silicon. Physica B: Condensed Matter, 2009, 404, 4681-4684.	1.3	2
225	Capacitance investigation of Ge nanoclusters on a silicon (001) surface grown by MBE at low temperatures. Physica B: Condensed Matter, 2009, 404, 4705-4707.	1.3	2
226	Influence of extended defects on gold diffusion in plastically deformed silicon. Journal of Surface Investigation, 2009, 3, 608-611.	0.1	2
227	Effect of contamination with iron on the electron-beam-induced current contrast of extended defects in multicrystalline silicon. Journal of Surface Investigation, 2012, 6, 897-900.	0.1	2
228	Rate of generation of nonequilibrium charge carriers by a focused X-ray beam. Journal of Surface Investigation, 2013, 7, 859-862.	0.1	2
229	Low energy electron beam irradiation effect on optical properties of nanopillar MQW InGaN/GaN structures. , 2014, , .		2
230	Quantitative description of the properties of extended defects in silicon by means of electron- and laser-beam-induced currents. Semiconductors, 2015, 49, 741-745.	0.2	2
231	Minority carrier diffusion length in Al <sub>x</sub> Ga <sub>1-x</sub> N (x = 0.1) grown by ammonia molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 447-450.	0.8	2
232	Dislocation glide in GaN films grown by the lateral-overgrowth method induced by low-energy electron-beam irradiation. Journal of Surface Investigation, 2016, 10, 959-961.	0.1	2
233	Investigation of stacking faults introduced into 4H-SiC crystals by indentation. Journal of Surface Investigation, 2017, 11, 234-237.	0.1	2
234	Study of Low Voltage Prebreakdown Sites in Multicrystalline Si Based Cells by the LBIC, EL, and EDS Methods. Advances in Condensed Matter Physics, 2017, 2017, 1-5.	0.4	2

#	ARTICLE	IF	CITATIONS
235	Structural investigation of light-emitting A3B5 structures grown on Ge/Si(100) substrate. Journal of Physics: Conference Series, 2018, 1124, 022037.	0.3	2
236	Estimation of the Maximum Nonequilibrium Charge-Carrier Concentration in GaN Under Electron-Beam Irradiation. Journal of Surface Investigation, 2018, 12, 1000-1004.	0.1	2
237	Structural and optical characteristics of GaAs films grown on Si/Ge substrates. Journal of Physics: Conference Series, 2018, 993, 012014.	0.3	2
238	New functional material: spark plasma sintered Si/SiO <sub>2</sub> nanoparticles " fabrication and properties. RSC Advances, 2019, 9, 16746-16753.	1.7	2
239	Effect of Nickel and Copper Introduced at Room Temperature on the Recombination Properties of Extended Defects in Silicon. Semiconductors, 2019, 53, 411-414.	0.2	2
240	Deep traps and persistent photocapacitance in $\text{In}^{2-}(\text{Al}_{0.14}\text{Ga}_{0.86})_2\text{O}_3/\text{Ga}_2\text{O}_3$ heterojunctions. Journal of Applied Physics, 2019, 125, .	1.1	2
241	Metal Impurities and Gettering in Crystalline Silicon. , 2019, , 495-540.		2
242	Comparative Study of Optical and Electrical Properties of Grown-In and Freshly Introduced Dislocations in GaN by SEM Methods. Journal of Electronic Materials, 2020, 49, 5173-5177.	1.0	2
243	Estimations of Activation Energy for Dislocation Mobility in p-GaN. ECS Journal of Solid State Science and Technology, 2021, 10, 026004.	0.9	2
244	Parasitic "n junctions formed at V-pit defects in p-GaN. Journal of Applied Physics, 2021, 129, 155702.	1.1	2
245	ASYMMETRY OF ISOLATED DISLOCATIONS MOBILITY IN Ge AND Si SINGLE CRYSTALS. Journal De Physique Colloque, 1983, 44, C4-85-C4-89.	0.2	2
246	SEM Characterization of Multilayer Structures. Acta Physica Polonica A, 1993, 83, 81-86.	0.2	2
247	Communication"Electron-Beam Stimulated Release of Dislocations from Pinning Sites in GaN. ECS Journal of Solid State Science and Technology, 2022, 11, 015003.	0.9	2
248	Effect of Compressive and Stretching Strains on the Dislocation Luminescence Spectrum in Silicon. Semiconductors, 2021, 55, 633.	0.2	2
249	Kink migration along 30° Si"core partial dislocations in 4H"SiC. Physica Status Solidi (A) Applications and Materials Science, 0, , .	0.8	2
250	Scanning deep level transient spectroscopy (SDLTS) investigations of deep level spatial distribution in implanted silicon. Journal of Crystal Growth, 1990, 103, 287-290.	0.7	1
251	Effect of Deep Level Athermal Recharging on DLTS Spectra in HgCdTe. Physica Status Solidi A, 1993, 136, 455-463.	1.7	1
252	E-beam tomography of planar semiconductor structures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 42, 52-56.	1.7	1

#	ARTICLE	IF	CITATIONS
253	Formation of Electrical Activity of Dislocations in Si during Plastic Deformation. Solid State Phenomena, 1996, 51-52, 15-20.	0.3	1
254	Influence of a subsurface layer on surface pyroelectric potential formation in lithium niobate. Ferroelectrics, 1997, 201, 175-183.	0.3	1
255	SEM-EBIC Study of Defects in Epitaxial AlGaIn Layers. Solid State Phenomena, 1998, 63-64, 131-138.	0.3	1
256	Metastable behavior of current-voltage characteristics in Hg <sub>1-x</sub> Cd <sub>x</sub> Te p-n junctions. , 2000, , .		1
257	Hydrogen-Related Defects in High-Resistivity Silicon. Solid State Phenomena, 2001, 82-84, 150-154.	0.3	1
258	Nitrogen Effect on Hydrogen Penetration into Cz Si during Wet Chemical Etching. Solid State Phenomena, 2002, 82-84, 145-149.	0.3	1
259	Computer simulation of excess carrier distribution for the phase shift microwave detected photoconductivity technique. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 91-92, 253-255.	1.7	1
260	Study of nitrogen-related defects by means of gold and hydrogen diffusion investigations. Microelectronic Engineering, 2003, 66, 379-384.	1.1	1
261	Effect of ECR Plasma Treatment on Lithium Niobate Surface State. Ferroelectrics, 2004, 300, 147-150.	0.3	1
262	EBIC and DLTS characterization of pure Si crystals. Bulletin of Materials Science, 2005, 28, 367-371.	0.8	1
263	DIFFUSION LENGTH AND EFFECTIVE CARRIER LIFETIME IN III-NITRIDES. International Journal of Nanoscience, 2007, 06, 323-326.	0.4	1
264	EBIC Investigations of Deformation Induced Defects in Si. Solid State Phenomena, 2007, 131-133, 529-534.	0.3	1
265	EBIC study of resistive photosensitive elements based on HgCdTe. Semiconductors, 2007, 41, 235-239.	0.2	1
266	Surface monitoring of HEMT structures. Superlattices and Microstructures, 2009, 45, 332-336.	1.4	1
267	Photo- and cathodoluminescence investigation of ZnO films. Journal of Surface Investigation, 2011, 5, 772-774.	0.1	1
268	SEM Investigation of the electrical properties of silicon ribbons. Journal of Surface Investigation, 2011, 5, 954-957.	0.1	1
269	XBIC using a laboratory X-ray source. Bulletin of the Russian Academy of Sciences: Physics, 2013, 77, 21-23.	0.1	1
270	Investigation of stacking faults in 4H-SiC using the electron-beam-induced current method. Journal of Surface Investigation, 2013, 7, 856-858.	0.1	1



#	ARTICLE	IF	CITATIONS
271	Temperature dependence of the cathodoluminescence spectra of irradiated light-emitting-diode structures with multiple InGaN/GaN quantum wells. Journal of Surface Investigation, 2013, 7, 844-847.	0.1	1
272	Studying stacking faults in SiC by the XBIC method using a laboratory X-ray source. Journal of Surface Investigation, 2014, 8, 155-157.	0.1	1
273	Inverse bias effect on the optical properties of light-emitting diodes with multiple InGaN/GaN quantum wells when irradiated by an electron beam in a scanning electron microscope. Journal of Surface Investigation, 2015, 9, 944-947.	0.1	1
274	Diffusion length and grain boundary recombination activity determination by means of induced current methods. Superlattices and Microstructures, 2016, 99, 108-112.	1.4	1
275	Physical properties of carbon films obtained by methane pyrolysis in an electric field. Technical Physics, 2016, 61, 428-431.	0.2	1
276	Comparative study of the spectral and structural properties of EuAl <sub>3</sub> (BO <sub>3</sub> ) <sub>4</sub> single crystals with different morphologies. Physics of the Solid State, 2017, 59, 2423-2429.	0.2	1
277	EBIC INVESTIGATIONS OF EXTENDED DEFECTS IN CdTe. European Physical Journal Special Topics, 1991, 01, C6-181-C6-186.	0.2	1
278	Prediction of Betavoltaic Battery Output Parameters Based on SEM Measurements. Journal of Nano- and Electronic Physics, 2016, 8, 04062-1-04062-3.	0.2	1
279	Effect of Electron-Beam Irradiation on the Cathodoluminescence of a ZnO Nanorod Array. Journal of Surface Investigation, 2021, 15, 1208-1211.	0.1	1
280	Dislocation Impurity Interaction and its Effect on Semiconductor Properties. Materials Research Society Symposia Proceedings, 1988, 138, 173.	0.1	0
281	Electrical Properties of Dislocation Impurity Atmospheres in Si. Solid State Phenomena, 1991, 19-20, 367-372.	0.3	0
282	Processes of Defect Formation and Gettering under Dry Etching of Si and GaAs and Measurements of Diffusion Length Profile. Solid State Phenomena, 1993, 32-33, 99-104.	0.3	0
283	Microcharacterization of Polycrystalline Semiconductors by Scanning Electron Microscopy in Electron Beam Induced Current Mode. Solid State Phenomena, 1996, 51-52, 39-50.	0.3	0
284	Annihilation of Self-Interstitials by Dislocations in Silicon as Studied by Gold Diffusion. Solid State Phenomena, 1996, 51-52, 3-14.	0.3	0
285	The Spatial Distribution of Modulated CL Signal in Inhomogeneous Semiconductors with Large Diffusion Length. Solid State Phenomena, 1998, 63-64, 199-206.	0.3	0
286	Reconstruction of Deep Level Defect Distribution from DLTS Measurements in Compensated Semiconductors. Solid State Phenomena, 1999, 69-70, 531-538.	0.3	0
287	Impurity Effect on the Dislocation DLTS Spectrum in Silicon. Solid State Phenomena, 1999, 67-68, 27-32.	0.3	0
288	Electrical Properties of Oxygen Precipitates Formed During Two Step Low Temperature Annealing. Solid State Phenomena, 1999, 67-68, 39-44.	0.3	0

#	ARTICLE	IF	CITATIONS
289	Reconstruction of diffusion length distributions in semiconductors by photocurrent measurements with the depletion region modulation. Journal of Applied Physics, 1999, 86, 5070-5074.	1.1	0
290	Gold Gettering by H <sup>+</sup> or He <sup>++</sup> Ion Implantation Induced Cavities and Defects in Cz Silicon Wafers. Solid State Phenomena, 2002, 82-84, 297-302.	0.3	0
291	Hydrogen Penetration into Si under Wet Chemical Etching: Experiment and Simulation. Solid State Phenomena, 2001, 80-81, 121-126.	0.3	0
292	Numerical simulation of the signal formation in a scanning electron microscope with remote electrodes. Journal of Physics Condensed Matter, 2002, 14, 13147-13152.	0.7	0
293	Determination of diffusion length by the surface electron beam induced voltage method. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 91-92, 256-259.	1.7	0
294	Leakage currents over the Surface of CdHgTe-based photodiodes. Semiconductors, 2004, 38, 855-860.	0.2	0
295	EBIC and DLTS Study of Deformation Induced Defect Thermal Stability in n-Si. Solid State Phenomena, 2005, 108-109, 567-570.	0.3	0
296	Study of Au Diffusion in Nitrogen-Doped FZ Si. Solid State Phenomena, 2005, 108-109, 241-244.	0.3	0
297	Electrical Characterisation of 4H-SiC Epitaxial Samples Treated by Hydrogen or Helium. Materials Science Forum, 2007, 556-557, 347-350.	0.3	0
298	Electron beam induced current investigation of planar photodiode structures on InSb crystals. Journal of Surface Investigation, 2007, 1, 44-48.	0.1	0
299	EBIC study of nonradiative recombination in silicon LEDs with near-band-edge luminescence. Semiconductors, 2010, 44, 1241-1243.	0.2	0
300	Luminescence of SiC films grown by a vapor phase reaction. Journal of Physics: Conference Series, 2011, 281, 012019.	0.3	0
301	Metastable hydrogen-related defects in epitaxial n-GaAs studied by Laplace deep level transient spectroscopy. , 2014, , .		0
302	Characterization of 4H-SiC pn Structures with Unstable Excess Current. Materials Science Forum, 2015, 821-823, 648-651.	0.3	0
303	Structural, electrical and luminescent characteristics of ultraviolet light emitting structures grown by hydride vapor phase epitaxy. Modern Electronic Materials, 2017, 3, 32-39.	0.2	0
304	Investigation of the Effect of Electron-Beam Irradiation on the Defect Structure of Laterally Overgrown GaN Films via the Induced-Current and Cathodoluminescence Methods. Journal of Surface Investigation, 2018, 12, 994-999.	0.1	0
305	Defect structure and properties of Zn diffusion doped Si after swift Xe ion irradiation. Journal of Physics: Conference Series, 2019, 1190, 012011.	0.3	0
306	Simulation of the Properties of Betavoltaic Cells Based on Silicon and <sup>63</sup> Ni Enriched Film. Journal of Surface Investigation, 2019, 13, 285-288.	0.1	0

#	ARTICLE	IF	CITATIONS
307	Dependence of the Bulk Electrical Properties of Multisilicon on the Grain Misorientation Parameters. Semiconductors, 2019, 53, 55-59.	0.2	0
308	Electron Beam Induced Current and Deep Level Transient Spectroscopy Study of Dislocation Trails in Au Doped Si. Physica Status Solidi (A) Applications and Materials Science, 0, , 2100095.	0.8	0
309	Investigation of the Effect of Irradiation by a Low-Energy Electron Beam on the Capacitance Voltage Characteristics of SiO <sub>2</sub> . Journal of Surface Investigation, 2021, 15, 1045-1048.	0.1	0
310	COMPUTER PROCESSING OF EBIC SIGNALS. European Physical Journal Special Topics, 1991, 01, C6-51-C6-56.	0.2	0
311	INVESTIGATION OF ELECTRICAL PROPERTY INHOMOGENEITIES FORMED BY PLASMA ETCHING. European Physical Journal Special Topics, 1991, 01, C6-217-C6-222.	0.2	0
312	NEW POSSIBILITIES OF EBIC FOR DISLOCATION STUDY. European Physical Journal Special Topics, 1991, 01, C6-193-C6-198.	0.2	0
313	Contactless mapping of electrical properties inhomogeneities by the surface electron beam induced voltage method. , 2017, , 75-78.		0
314	Reconstruction of electrical properties distribution around extended defects with submicron spatial resolution based on the SEM-EBIC measurement. , 2017, , 79-82.		0
315	SEM investigations of individual extended defects in GaN epilayers. , 2018, , 597-600.		0
316	Metal Impurities and Gettering in Crystalline Silicon. , 2019, , 1-46.		0
317	Influence of the Structural Parameters of Triple Junctions of Special Grain Boundaries on Their Recombination Activity. Journal of Surface Investigation, 2021, 15, S1-S6.	0.1	0